

TRANSISTOR MODULE (THREE PHASES BRIDGE TYPE)

QF15AA40/60

TOP

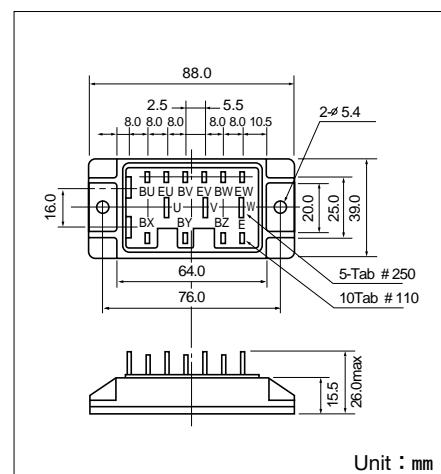
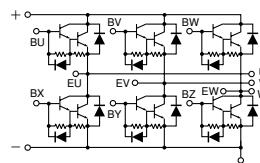


QF15AA is six pack Darlington power transistor module which has six transistors connected in three phase bridge configuration. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction.

- $I_c = 15A$, $V_{CEX} = 400/600V$
- Low saturation voltage for higher efficiency.
- High DC current gain h_{FE}
- Isolated mounting base
- $V_{EBO} 10V$ for faster switching speed.

(Applications)

Motor Control (VVVF), AC Servo, UPS



Unit : mm

($T_j = 25^\circ C$ unless otherwise specified)

■ Maximum Ratings

Symbol	Item	Conditions	Ratings		Unit
			QF15AA40	QF15AA60	
V_{CBO}	Collector-Base Voltage		400	600	V
V_{CEX}	Collector-Emitter Voltage	$V_{BE} = -2V$	400	600	V
V_{EBO}	Emitter-Base Voltage			10	V
I_c	Collector Current	() = $pw \leq 1ms$		15 (30)	A
$-I_c$	Reverse Collector Current			15	A
I_B	Base Current			1	A
P_T	Total power dissipation	$T_c = 25^\circ C$		100	W
T_j	Junction Temperature			-40 to +150	°C
T_{stg}	Storage Temperature			-40 to +125	°C
V_{iso}	Isolation Voltage	A.C.1minute		2500	V
	Mounting Torque (M5)	Recommended Value 1.5-2.5 (15-25)		2.7 (28)	N·m (kgf·cm)
	Mass	Typical Value		95	g

■ Electrical Characteristics

Symbol	Item	Conditions	Ratings		Unit
			Min.	Max.	
I_{CBO}	Collector Cut-off Current	$V_{CB} = V_{CBO}$		1.0	mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = V_{EBO}$		100	mA
$V_{CEO(sus)}$	Collector Emitter Sustaining Voltage	$QF15AA40$ $QF15AA60$	$I_c = 1A$	300	V
				450	
$V_{CEX(sus)}$		$QF15AA40$ $QF15AA60$	$I_c = 3A$, $I_{B2} = -1A$	400	V
				600	
h_{FE}	DC Current Gain		$I_c = 15A$, $V_{CE} = 2V$	75	
			$I_c = 15A$, $V_{CE} = 5V$	100	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_c = 15A$, $I_B = 0.2A$		2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_c = 15A$, $I_B = 0.2A$		2.5	V
t_{on}	Switching Time	On Time	$V_{cc} = 300V$, $I_c = 15A$ $I_{B1} = 0.4A$, $I_{B2} = -0.4A$	1.0	μs
t_s		Storage Time		12.0	
t_f		Fall Time		2.0	
V_{ECO}	Collector-Emitter Reverse Voltage	$-I_c = 15A$		1.5	V
$R_{th(j-c)}$	Thermal Impedance (junction to case)	Transistor part		1.2	$^\circ C/W$
		Diode part		2.5	

